Bo Shen

List of Publications by Year
in descending order

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146	3,354	147566	182168
papers	citations	31 h-index	51 g-index

146	146	146	4443
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Generation and electric control of spinâ€“valley-coupled circular photogalvanic current in WSe2. Nature Nanotechnology, 2014, 9, 851-857.	15.6	278
2	High-Performance Normally-Off ${m Al}_{2}{m O}_{3}/{m GaN}$ MOSFET Using a Wet Etching-Based Gate Recess Technique. IEEE Electron Device Letters, 2013, 34, 1370-1372.	2.2	167
3	Role of the Excitonâ€“Polariton in a Continuous-Wave Optically Pumped CsPbBr₃ Perovskite Laser. Nano Letters, 2020, 20, 6636-6643.	4.5	145
4	High-quality AlN epitaxy on nano-patterned sapphire substrates prepared by nano-imprint lithography. Scientific Reports, 2016, 6, 35934.	1.6	110
5	Tailoring MoS₂ Valleyâ€Polarized Photoluminescence with Super Chiral Nearâ€Field. Advanced Materials, 2018, 30, e1801908.	11.1	99
6	Ultrathin-Barrier AlGaN/GaN Heterostructure: A Recess-Free Technology for Manufacturing High-Performance GaN-on-Si Power Devices. IEEE Transactions on Electron Devices, 2018, 65, 207-214.	1.6	87
7	Plasmonicâ€Functionalized Broadband Perovskite Photodetector. Advanced Optical Materials, 2018, 6, 1701271.	3.6	86
8	Effect of asymmetric Schottky barrier on GaN-based metal-semiconductor-metal ultraviolet detector. Applied Physics Letters, 2011, 99, .	1.5	84
9	900 V/1.6 <inline-formula> <tex-math notation="TeX">${m m}Omegacdot{m cm}^{2}$ </tex-math></inline-formula> Normally Off <inline-formula> <tex-math notation="TeX">${m Al}_{2}{m O}_{3}/{m GaN}$ </tex-math></inline-formula> MOSFET on Silicon Substrate. IEEE Transactions on Electron Devices, 2014, 61, 2035-2040.	1.6	79
10	Highâ€Outputâ€Power Ultraviolet Light Source from Quasiâ€2D GaN Quantum Structure. Advanced Materials, 2016, 28, 7978-7983.	11.1	72
11	Self-Learning Perfect Optical Chirality via a Deep Neural Network. Physical Review Letters, 2019, 123, 213902.	2.9	72
12	K-Î› crossover transition in the conduction band of monolayer MoS ₂ under hydrostatic pressure. Science Advances, 2017, 3, e1700162.	4.7	60
13	Investigation of Surface- and Buffer-Induced Current Collapse in GaN High-Electron Mobility Transistors Using a Soft Switched Pulsed (I-V) Measurement. IEEE Electron Device Letters, 2014, 35, 1094-1096.	2.2	54
14	Growth of high quality and uniformity AlGaN/GaN heterostructures on Si substrates using a single AlGaN layer with low Al composition. Scientific Reports, 2016, 6, 23020.	1.6	52
15	A GaN HEMT Structure Allowing Self-Terminated, Plasma-Free Etching for High-Uniformity, High-Mobility Enhancement-Mode Devices. IEEE Electron Device Letters, 2016, 37, 377-380.	2.2	52
16	Identification of Helicity-Dependent Photocurrents from Topological Surface States in Bi2Se3 Gated by Ionic Liquid. Scientific Reports, 2014, 4, 4889.	1.6	51
17	Epitaxy of Singleâ€Crystalline GaN Film on CMOSâ€Compatible Si(100) Substrate Buffered by Graphene. Advanced Functional Materials, 2019, 29, 1905056.	7.8	51
18	Quasi-Vertical GaN Schottky Barrier Diode on Silicon Substrate With 10¹⁰ High On/Off Current Ratio and Low Specific On-Resistance. IEEE Electron Device Letters, 2020, 41, 329-332.	2.2	51

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19	Unambiguous Identification of Carbon Location on the N Site in Semi-insulating GaN. Physical Review Letters, 2018, 121, 145505.	2.9	45
20	High-Quality AlN Film Grown on Sputtered AlN/Sapphire via Growth-Mode Modification. Crystal Growth and Design, 2018, 18, 6816-6823.	1.4	45
21	Low ON-Resistance GaN Schottky Barrier Diode With High <inline-formula> <tex-math notation="LaTeX">$V_{mathrm{ON}}$ </tex-math> </inline-formula> Uniformity Using LPCVD Si₃N₄ Compatible Self-Terminated, Low Damage Anode Recess Technology. IEEE Electron Device Letters, 2018, 39, 859-862.	2.2	44
22	Rashba and Dresselhaus spin-orbit coupling in GaN-based heterostructures probed by the circular photogalvanic effect under uniaxial strain. Applied Physics Letters, 2010, 97, .	1.5	43
23	Deep-level traps induced dark currents in extended wavelength InxGa1â^'xAs/InP photodetector. Journal of Applied Physics, 2013, 114, .	1.1	43
24	Characterization of 880 V Normally Off GaN MOSHEMT on Silicon Substrate Fabricated With a Plasma-Free, Self-Terminated Gate Recess Process. IEEE Transactions on Electron Devices, 2018, 65, 1453-1457.	1.6	43
25	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. Advanced Optical Materials, 2019, 7, 1801763.	3.6	43
26	Grapheneâ€Assisted Epitaxy of Nitrogen Lattice Polarity GaN Films on Nonâ€Polar Sapphire Substrates for Green Light Emitting Diodes. Advanced Functional Materials, 2020, 30, 2001283.	7.8	41
27	Temperature Dependence of the Surface- and Buffer-Induced Current Collapse in GaN High-Electron Mobility Transistors on Si Substrate. IEEE Transactions on Electron Devices, 2015, 62, 2475-2480.	1.6	36
28	Lattice-Polarity-Driven Epitaxy of Hexagonal Semiconductor Nanowires. Nano Letters, 2016, 16, 1328-1334.	4.5	35
29	Single-Photon Emission from Point Defects in Aluminum Nitride Films. Journal of Physical Chemistry Letters, 2020, 11, 2689-2694.	2.1	35
30	High quality AlN epilayers grown on nitrided sapphire by metal organic chemical vapor deposition. Scientific Reports, 2017, 7, 42747.	1.6	33
31	Investigation on entraining and enhancing human circadian rhythm in closed environments using daylight-like LED mixed lighting. Science of the Total Environment, 2020, 732, 139334.	3.9	33
32	Deepâ€Ultraviolet Microâ€LEDs Exhibiting High Output Power and High Modulation Bandwidth Simultaneously. Advanced Materials, 2022, 34, e2109765.	11.1	33
33	Repeatable Room Temperature Negative Differential Resistance in AlN/GaN Resonant Tunneling Diodes Grown on Sapphire. Advanced Electronic Materials, 2019, 5, 1800651.	2.6	32
34	Gate-Recessed Normally OFF GaN MOSHEMT With High-Temperature Oxidation/Wet Etching Using LPCVD Si₃N₄as the Mask. IEEE Transactions on Electron Devices, 2018, 65, 1728-1733.	1.6	31
35	Schottky-MOS Hybrid Anode AlGaN/GaN Lateral Field-Effect Rectifier With Low Onset Voltage and Improved Breakdown Voltage. IEEE Electron Device Letters, 2017, 38, 1425-1428.	2.2	29
36	Flexibly and Repeatedly Modulating Lasing Wavelengths in a Single Coreâ€“Shell Semiconductor Microrod. ACS Nano, 2017, 11, 5808-5814.	7.3	26

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37	A study of GaN nucleation and coalescence in the initial growth stages on nanoscale patterned sapphire substrates via MOCVD. CrystEngComm, 2018, 20, 6811-6820.	1.3	26
38	Mechanism of stress-driven composition evolution during hetero-epitaxy in a ternary AlGaN system. Scientific Reports, 2016, 6, 25124.	1.6	25
39	The effects of nanocavity and photonic crystal in InGaN/GaN nanorod LED arrays. Nanoscale Research Letters, 2016, 11, 340.	3.1	25
40	Deep subwavelength control of valley polarized cathodoluminescence in h-BN/WSe2/h-BN heterostructure. Nature Communications, 2021, 12, 291.	5.8	25
41	Evidence of Type-II Band Alignment in III-nitride Semiconductors: Experimental and theoretical investigation for In0.17Al0.83N/GaN heterostructures. Scientific Reports, 2014, 4, 6521.	1.6	23
42	Study on Light Extraction from GaN-based Green Light-Emitting Diodes Using Anodic Aluminum Oxide Pattern and Nanoimprint Lithography. Scientific Reports, 2016, 6, 21573.	1.6	23
43	Al diffusion at AlN/Si interface and its suppression through substrate nitridation. Applied Physics Letters, 2020, 116, .	1.5	23
44	2.6 Î¼m MBE grown InGaAs detectors with dark current of SRH and TAT. AIP Advances, 2014, 4, .	0.6	22
45	High-electron-mobility InN epilayers grown on silicon substrate. Applied Physics Letters, 2018, 112, .	1.5	22
46	Sub-nanometer ultrathin epitaxy of AlGaN and its application in efficient doping. Light: Science and Applications, 2022, 11, 71.	7.7	22
47	Experimental Evidence of Large Bandgap Energy in Atomically Thin AlN. Advanced Functional Materials, 2019, 29, 1902608.	7.8	21
48	Free and bound excitonic effects in Al0.5Ga0.5N/Al0.35Ga0.65N MQWs with different Si-doping levels in the well layers. Scientific Reports, 2015, 5, 13046.	1.6	20
49	Single-photon emission from isolated monolayer islands of InGaN. Light: Science and Applications, 2020, 9, 159.	7.7	20
50	Interface charge engineering in down-scaled AlGaN (<6â€‰nm)/GaN heterostructure for fabrication of GaN-based power HEMTs and MIS-HEMTs. Applied Physics Letters, 2020, 116, .	1.5	20
51	Vacancy-engineering-induced dislocation inclination in III-nitrides on Si substrates. Physical Review Materials, 2020, 4, .	0.9	20
52	Reduction of Current Collapse in GaN High-Electron Mobility Transistors Using a Repeated Ozone Oxidation and Wet Surface Treatment. IEEE Electron Device Letters, 2015, 36, 757-759.	2.2	19
53	Gate-Recessed Normally-OFF GaN MOSHEMT With Improved Channel Mobility and Dynamic Performance Using AlN/Si₃N₄ as Passivation and Post Gate-Recess Channel Protection Layers. IEEE Electron Device Letters, 2017, 38, 1075-1078.	2.2	19
54	Inversion Symmetry Breaking Induced Valley Hall Effect in Multilayer WSe₂. ACS Nano, 2019, 13, 9325-9331.	7.3	19

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55	Lattice Polarity Manipulation of Quasiâ€vdW Epitaxial GaN Films on Graphene Through Interface Atomic Configuration. Advanced Materials, 2022, 34, e2106814.	11.1	19
56	Local surface plasmon enhanced polarization and internal quantum efficiency of deep ultraviolet emissions from AlGaN-based quantum wells. Scientific Reports, 2017, 7, 2358.	1.6	18
57	Photon wavelength dependent valley photocurrent in multilayer <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow><mml:mi>MoS</mml:mi></mml:mrow><mml:mn>2 Physical Review B, 2017, 96, .	1.1	18
58	Singleâ€photon emission from a further confined InGaN/GaN quantum disc via reverseâ€reaction growth. Quantum Engineering, 2019, 1, e20.	1.2	18
59	Temperature sensitive photoconductivity observed in InN layers. Applied Physics Letters, 2013, 102, .	1.5	17
60	Electronic properties of polycrystalline graphene under large local strain. Applied Physics Letters, 2014, 104, .	1.5	17
61	Latticeâ€Symmetryâ€Driven Epitaxy of Hierarchical GaN Nanotripods. Advanced Functional Materials, 2017, 27, 1604854.	7.8	17
62	Selectively steering photon spin angular momentum via electron-induced optical spin Hall effect. Science Advances, 2021, 7, .	4.7	17
63	Effects of interface oxidation on the transport behavior of the two-dimensional-electron-gas in AlGaN/GaN heterostructures by plasma-enhanced-atomic-layer-deposited AlN passivation. Journal of Applied Physics, 2013, 114, .	1.1	16
64	Molecular beam epitaxy of single-crystalline aluminum film for low threshold ultraviolet plasmonic nanolasers. Applied Physics Letters, 2018, 112, .	1.5	15
65	Exciton emission of quasi-2D InGaN in GaN matrix grown by molecular beam epitaxy. Scientific Reports, 2017, 7, 46420.	1.6	14
66	Realization of high efficiency AlGaN-based multiple quantum wells grown on nano-patterned sapphire substrates. CrystEngComm, 2021, 23, 1201-1206.	1.3	14
67	Effect of Grain Boundary Scattering on Electron Mobility of N-Polarity InN Films. Applied Physics Express, 2013, 6, 021001.	1.1	13
68	Development trends of GaN-based wide bandgap semiconductors: from solid state lighting to power electronic devices. Frontiers of Optoelectronics, 2015, 8, 456-460.	1.9	13
69	High quality AlN film grown on a nano-concave-circle patterned Si substrate with an AlN seed layer. Applied Physics Letters, 2020, 117, .	1.5	13
70	Direct evidence of hydrogen interaction with carbon: Câ€“H complex in semi-insulating GaN. Applied Physics Letters, 2020, 116, .	1.5	12
71	Controlling Phaseâ€Coherent Electron Transport in IIIâ€Nitrides: Toward Room Temperature Negative Differential Resistance in AlGaN/GaN Double Barrier Structures. Advanced Functional Materials, 2021, 31, 2007216.	7.8	12
72	High quality GaN-on-SiC with low thermal boundary resistance by employing an ultrathin AlGaN buffer layer. Applied Physics Letters, 2021, 118, .	1.5	12

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73	Wide bandgap semiconductor materials and devices. Journal of Applied Physics, 2022, 131, .	1.1	12
74	Determination of the surface band bending in In_xGa_{1â^'x}N films by hard x-ray photoemission spectroscopy. Science and Technology of Advanced Materials, 2013, 14, 015007.	2.8	11
75	Spin transport study in a Rashba spin-orbit coupling system. Scientific Reports, 2014, 4, 4030.	1.6	11
76	Enhanced transport properties in InAlGaN/AlN/GaN heterostructures on Si (111) substrates: The role of interface quality. Applied Physics Letters, 2017, 110, .	1.5	11
77	Single photon source based on an InGaN quantum dot in a site-controlled optical horn structure. Applied Physics Letters, 2019, 115, .	1.5	11
78	Dominant Influence of Interface Roughness Scattering on the Performance of GaN Terahertz Quantum Cascade Lasers. Nanoscale Research Letters, 2019, 14, 206.	3.1	11
79	Three Subband Occupation of the Twoâ€Dimensional Electron Gas in Ultrathin Barrier AlN/GaN Heterostructures. Advanced Functional Materials, 2020, 30, 2004450.	7.8	11
80	Strain-enhanced high Q-factor GaN micro-electromechanical resonator. Science and Technology of Advanced Materials, 2020, 21, 515-523.	2.8	11
81	Electrical Spin Injection into the 2D Electron Gas in AlN/GaN Heterostructures with Ultrathin AlN Tunnel Barrier. Advanced Functional Materials, 2021, 31, 2009771.	7.8	11
82	Control of dislocations in heteroepitaxial AlN films by extrinsic supersaturated vacancies introduced through thermal desorption of heteroatoms. Applied Physics Letters, 2021, 118, .	1.5	11
83	Hydrogen-Modulated Step Graded Junction Termination Extension in GaN Vertical p-n Diodes. IEEE Electron Device Letters, 2021, 42, 1124-1127.	2.2	11
84	Formation of p-n-p junction with ionic liquid gate in graphene. Applied Physics Letters, 2014, 104, .	1.5	10
85	Band offsets of non-polar A-plane GaN/AlN and AlN/GaN heterostructures measured by X-ray photoemission spectroscopy. Nanoscale Research Letters, 2014, 9, 470.	3.1	10
86	Study on AlGaN P-I-N-I-N solar-blind avalanche photodiodes with Al0.45Ga0.55N multiplication layer. Electronic Materials Letters, 2015, 11, 1053-1058.	1.0	10
87	The effects of dynamic daylight-like light on the rhythm, cognition, and mood of irregular shift workers in closed environment. Scientific Reports, 2021, 11, 13059.	1.6	10
88	Gate/Drain Coupled Barrier Lowering Effect and Negative Threshold Voltage Shift in Schottky-Type p-GaN Gate HEMT. IEEE Transactions on Electron Devices, 2022, 69, 3630-3635.	1.6	10
89	High Voltage Vertical GaN-on-GaN Schottky Barrier Diode with High Energy Fluorine Ion Implantation Based on Space Charge Induced Field Modulation (SCIFM) Effect. , 2020, , .		9
90	Low-Defect-Density Aluminum Nitride (AlN) Thin Films Realized by Zigzag Macrostep-Induced Dislocation Redirection. Crystal Growth and Design, 2021, 21, 3394-3400.	1.4	9

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91	Vertical leakage induced current degradation and relevant traps with large lattice relaxation in AlGaN/GaN heterostructures on Si. Applied Physics Letters, 2018, 112, 032104.	1.5	8
92	Fabrication of nano-patterned sapphire substrates by combining nanoimprint lithography with edge effects. CrystEngComm, 2019, 21, 1794-1800.	1.3	8
93	Spontaneous Emission of Plasmonâ€Exciton Polaritons Revealed by Ultrafast Nonradiative Decays. Laser and Photonics Reviews, 2020, 14, 2000233.	4.4	8
94	Edge Dislocations Triggered Surface Instability in Tensile Epitaxial Hexagonal Nitride Semiconductor. ACS Applied Materials & Interfaces, 2016, 8, 34108-34114.	4.0	7
95	Investigation of carrier compensation traps in nâ^'-GaN drift layer by high-temperature deep-level transient spectroscopy. Applied Physics Letters, 2020, 117, .	1.5	7
96	Spin relaxation induced by interfacial effects in n-GaN/MgO/Co spin injectors. RSC Advances, 2020, 10, 12547-12553.	1.7	7
97	GaN-based substrates and optoelectronic materials and devices. Science Bulletin, 2014, 59, 1201-1218.	1.7	6
98	Hot electron induced non-saturation current behavior at high electric field in InAlN/GaN heterostructures with ultrathin barrier. Scientific Reports, 2016, 6, 37415.	1.6	6
99	Buffer-Induced Time-Dependent OFF-State Leakage in AlGaN/GaN High Electron Mobility Transistors on Silicon. IEEE Transactions on Electron Devices, 2016, 63, 4860-4864.	1.6	6
100	Study on the Coupling Mechanism of the Orthogonal Dipoles with Surface Plasmon in Green LED by Cathodoluminescence. Nanomaterials, 2018, 8, 244.	1.9	6
101	Effect of unintentional nitrogen incorporation on n-type doping of Î²-Ga₂O₃grown by molecular beam epitaxy. CrystEngComm, 2022, 24, 269-274.	1.3	6
102	Polarizationâ€Drivenâ€Orientation Selective Growth of Singleâ€Crystalline IIIâ€Nitride Semiconductors on Arbitrary Substrates. Advanced Functional Materials, 2022, 32, .	7.8	6
103	Kilovolt GaN MOSHEMT on silicon substrate with breakdown electric field close to the theoretical limit. , 2017, , .		5
104	Planar anisotropic Shubnikov-de-Haas oscillations of two-dimensional electron gas in AlN/GaN heterostructure. Applied Physics Letters, 2019, 115, 152107.	1.5	5
105	Study on Electron-Induced Surface Plasmon Coupling with Quantum Well Using a Perturbation Method. Nanomaterials, 2020, 10, 913.	1.9	5
106	Epitaxial growth mechanisms of single-crystalline GaN on single-crystalline graphene. CrystEngComm, 2021, 23, 5451-5455.	1.3	5
107	Suppressing Buffer-Induced Current Collapse in GaN HEMTs with a Source-Connected p-GaN (SCPG): A Simulation Study. Electronics (Switzerland), 2021, 10, 942.	1.8	5
108	High-mobility nâ^'-GaN drift layer grown on Si substrates. Applied Physics Letters, 2021, 118, .	1.5	5

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109	Anisotropic strain relaxation and high quality AlGaN/GaN heterostructures on Si (110) substrates. Applied Physics Letters, 2017, 110, .	1.5	5
110	Study on Localized Surface Plasmon Coupling with Many Radiators. Nanomaterials, 2021, 11, 3105.	1.9	5
111	Utilization of far-red LED to minimize blue light hazard for dynamic semiconductor lighting. LEUKOS - Journal of Illuminating Engineering Society of North America, 2023, 19, 53-70.	1.5	5
112	Fe-doped InN layers grown by molecular beam epitaxy. Applied Physics Letters, 2012, 101, 171905.	1.5	4
113	Improving Performance of Alganâ€Based Deepâ€Ultraviolet Lightâ€Emitting Diodes by Inserting a Higher Alâ€Content Algan Layer Within the Multiple Quantum Wells. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700461.	0.8	4
114	Spin dynamics in GaN/Al0.1Ga0.9N quantum well with complex band edge structure. Applied Physics Letters, 2021, 118, 252107.	1.5	4
115	Enhanced Device Performance of AlGaN/GaN High Electron Mobility Transistors with Thermal Oxidation Treatment. Japanese Journal of Applied Physics, 2011, 50, 04DF10.	0.8	3
116	Magneto-transport Spectroscopy of the First and Second Two-dimensional Subbands in Al0.25Ga0.75N/GaN Quantum Point Contacts. Scientific Reports, 2017, 7, 42974.	1.6	3
117	Anomalous surface potential behavior observed in InN by photoassisted Kelvin probe force microscopy. Applied Physics Letters, 2017, 110, 222103.	1.5	3
118	Impact of Silicon Substrate with Low Resistivity on Vertical Leakage Current in AlGaN/GaN HEMTs. Applied Sciences (Switzerland), 2019, 9, 2373.	1.3	3
119	Cathodoluminescence nano-characterization of individual GaN/AlN quantum disks embedded in nanowires. Applied Physics Letters, 2020, 117, 133106.	1.5	3
120	Excitonic effects on electron spin orientation and relaxation in wurtzite GaN. Physical Review B, 2021, 104, .	1.1	3
121	High-Performance Quasi-Vertical GaN Schottky Barrier Diode on Silicon Substrate with a Low Dislocation Density Drift Layer. , 2019, , .		2
122	Multi-chip dynamic white light emitting diode with high level photobiological safety and good color fidelity. , 2019, , .		2
123	Graphene Acoustic Phononâ€Mediated Pseudoâ€Landau Levels Tailoring Probed by Scanning Tunneling Spectroscopy. Small, 2020, 16, 1905202.	5.2	2
124	Influence of intrinsic or extrinsic doping on charge state of carbon and its interaction with hydrogen in GaN. Applied Physics Letters, 2022, 120, .	1.5	2
125	Low-Resistive Ohmic Contacts in High-Electron-Mobility AlN/GaN Heterostructures by Suppressing the Oxygen Incorporation. ACS Applied Electronic Materials, 2022, 4, 3632-3639.	2.0	2
126	Influence of the illumination on the subband structure andÂoccupation in Al x Ga1â^'x N/GaN heterostructures. Applied Physics A: Materials Science and Processing, 2009, 96, 953-957.	1.1	1

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127	Study of diffusion and thermal stability of fluorine ions in GaN by Time-of-Flight Secondary Ion Mass Spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S952-S955.	0.8	1
128	Measurement of the Transport Property of 2-DEG in AlGaN/GaN Heterostructures Based on Circular Transmission Line Modeling of Two Concentric-Circle Schottky Contacts. IEEE Transactions on Electron Devices, 2018, 65, 3163-3168.	1.6	1
129	Enhanced Hydrogen Detection Based on Mg-Doped InN Epilayer. Sensors, 2018, 18, 2065.	2.1	1
130	GaNâ€onâ€Si(100): Epitaxy of Singleâ€Crystalline GaN Film on CMOSâ€Compatible Si(100) Substrate Buffered by Graphene (Adv. Funct. Mater. 42/2019). Advanced Functional Materials, 2019, 29, 1970293.	7.8	1
131	The in-plane anisotropy of the effective g factors in Al0.25Ga0.75N/GaN based quantum point contacts with narrow channels. Applied Physics Letters, 2020, 116, 182101.	1.5	1
132	Impact of Quantum Dots on III-Nitride Lasers: A Theoretical Calculation on Linewidth Enhancement Factors. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-7.	1.9	1
133	Improvement in Modulation Bandwidth of Micro-LED Arrays Based on Low-Temperature-Interlayer Approach. IEEE Photonics Technology Letters, 2022, 34, 675-678.	1.3	1
134	Low ON-Resistance Fully-Vertical GaN-on-SiC Schottky Barrier Diode with Conductive Buffer Layer. , 2022, , .		1
135	Transport and spin properties of the two-dimensional electron gas in GaN-based heterostructures. , 2008, , .		0
136	Crystalline quality of In<inf>x</inf>Al<inf>1-x</inf>N with different indium contents around lattice-matched to GaN. , 2008, , .		0
137	Effect of AlN interlayer thickness on leakage currents in Schottky contacts to Al<inf>0.25</inf>Ga<inf>0.75</inf>N/AlN/GaN heterostructures. , 2008, , .		0
138	Magnetotransport properties of the two-dimensional electron gas in AlxGa1-xN/GaN heterostructures under illumination. , 2008, , .		0
139	Enhanced wet etching of patterned GaN with heavy-ion implantation. , 2010, , .		0
140	Multiple Ti/Al stacks induced thermal stability enhancement in Ti/Al/Ni/Au Ohmic contact on AlGaN/GaN heterostructure. , 2010, , .		0
141	Circular photogalvanic effect in CdSe nanowires at room temperature. , 2016, , .		0
142	Study on 3D thermal transport in micro-LEDs on GaN substrate at the level of kW/cm2. , 2019, , .		0
143	Direct-readout pressure sensor based on AlGaN/GaN heterostructure. Microsystem Technologies, 2020, 26, 3189-3192.	1.2	0
144	Many-body Effects on the High Injection Level Performance for Micro Light Emitting Diode. , 2020, , .		0

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145	Lattice Polarity Manipulation of Quasiâ€vdW Epitaxial GaN Films on Graphene Through Interface Atomic Configuration (Adv. Mater. 5/2022). Advanced Materials, 2022, 34, .	11.1	0
146	Polarizationâ€Drivenâ€Orientation Selective Growth of Singleâ€Crystalline IIIâ€Nitride Semiconductors on Arbitrary Substrates (Adv. Funct. Mater. 14/2022). Advanced Functional Materials, 2022, 32, .	7.8	0